

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cabral et al.

Serial No.: 09/902,483

Filed: July 11, 2001



Group Art Unit: 2813

Examiner: Erik Kielin

TECHNOLOGY CENTER 2800

JAN - 6 2003

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For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY CONTACTS TO THIN FILM SILICON-ON-INSULATOR AND BULK MOSFETS AND FOR SHALLOW JUNCTIONS

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

EXCESS CLAIM FEE PAYMENT LETTER

Sir:

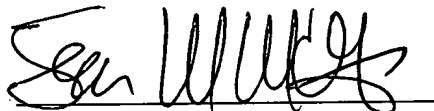
Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	28 -	22	= 6	x \$18.00	\$ 108.00
Indep. Claims	6 -	6	= 0	x \$84.00	\$ 0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$ 108.00

The Commissioner is authorized to charge Assignee's Deposit Account No. 50-0510 in the amount of \$108.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed. The Commissioner is authorized to charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 50-0510.

Respectfully Submitted,

Date: 1/2/03


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AND FOR SHALLOW JUNCTIONS

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated October 1, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

1. (Amended) A method for fabricating a silicide for a semiconductor device, said method comprising:
- depositing a metal containing silicon or a metal alloy on a silicon substrate,
 - reacting said metal containing silicon or said alloy to form a first silicide phase;
 - etching any unreacted metal containing silicon or alloy;
 - depositing a silicon cap layer over said first silicide phase;
 - reacting the silicon cap layer to form a second silicide phase, for said semiconductor device; and

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